Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS305PX

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- High-voltage DC-to-DC conversion
- · High-voltage MOSFET gate driving
- High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- · Automotive applications

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| V _{CEO} | collector-emitter voltage | open base | - | - | 80 | V |
| I _C | collector current | | - | - | 4.6 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | - | - | 9.2 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 38 | 53 | mΩ |



80 V, 4.6 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | E | emitter | | С |
| 2 | С | collector | | |
| 3 | В | base | 3 2 1 | B — (|
| | | | SOT89 | sym123 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | ^v ackage | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PBSS305NX | SOT89 | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS305NX | %5F |

[1] % = placeholder for manufacturing site code

80 V, 4.6 A NPN low VCEsat transistor

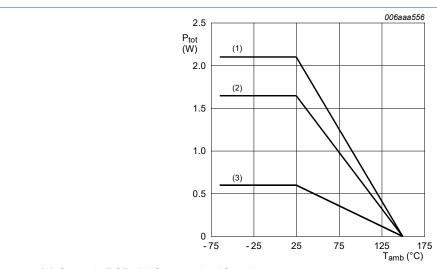
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | 80 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 80 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 5 | V |
| I _C | collector current | | | - | 4.6 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | 9.2 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 0.6 | W |
| | | | [2] | - | 1.65 | W |
| | | | [3] | - | 2.1 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint. [3]



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves**

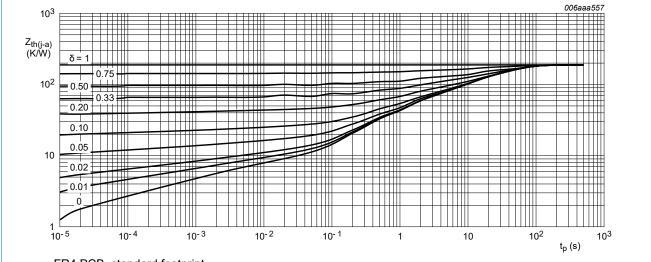
80 V, 4.6 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| ui(j-a) | thermal resistance from junction to ambient | in free air | [1] | - | - | 208 | K/W |
| | | | [2] | - | - | 76 | K/W |
| | | | [3] | - | - | 60 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

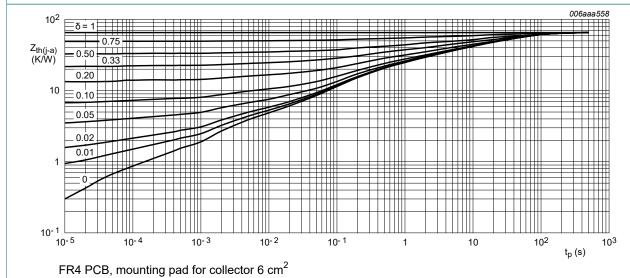
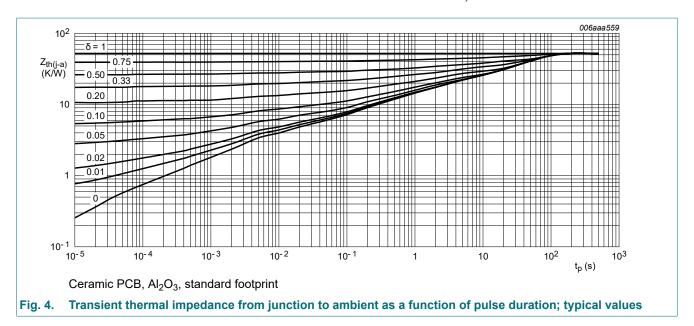


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

80 V, 4.6 A NPN low VCEsat transistor



80 V, 4.6 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|---|-----|------|------|------|
| I _{CBO} | collector-base cut-off | V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| | current | $V_{CB} = 80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$ | - | - | 50 | μA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| h _{FE} | DC current gain | V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 300 | 470 | - | |
| | | V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 250 | 420 | - | |
| | | V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C | 180 | 280 | - | |
| | | V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 90 | 140 | - | |
| | | V_{CE} = 2 V; I_{C} = 5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 70 | 110 | - | |
| V _{CEsat} | collector-emitter saturation voltage | I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 25 | 40 | mV |
| | | I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 50 | 70 | mV |
| | | I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 85 | 120 | mV |
| | | I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 105 | 140 | mV |
| | | I_C = 4 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 150 | 210 | mV |
| | | I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 140 | 200 | mV |
| | | I_C = 4 A; I_B = 80 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 210 | 320 | mV |
| | | I_C = 4.6 A; I_B = 230 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 170 | 240 | mV |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 38 | 53 | mΩ |
| | | I_C = 4 A; I_B = 80 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 53 | 80 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 0.82 | 0.9 | V |
| | | I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 0.94 | 1.05 | V |
| √ _{BEon} | base-emitter turn-on voltage | V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 0.77 | 0.85 | V |
| d | delay time | V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 0.15 A; | - | 15 | - | ns |
| r | rise time | I _{Boff} = -0.15 A; T _{amb} = 25 °C | - | 200 | - | ns |
| on | turn-on time | | - | 215 | - | ns |
| s | storage time | | - | 310 | - | ns |
| f | fall time | | - | 245 | - | ns |
| off | turn-off time |] | - | 555 | - | ns |

80 V, 4.6 A NPN low VCEsat transistor

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|-----------------------|---|-----|-----|-----|------|
| f _T | transition frequency | V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C | - | 110 | - | MHz |
| C _c | collector capacitance | V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | - | 30 | 50 | pF |

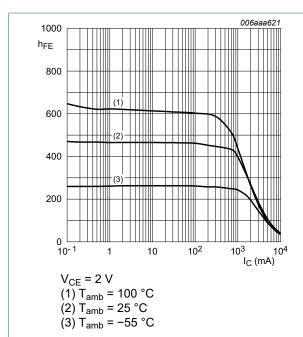


Fig. 5. DC current gain as a function of collector current; typical values

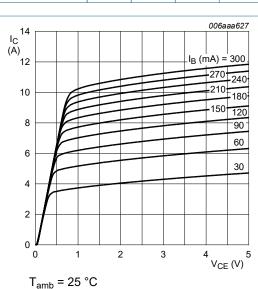


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

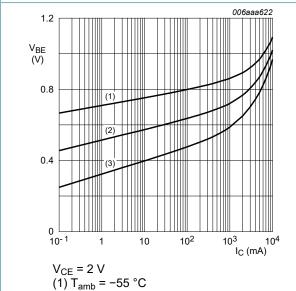
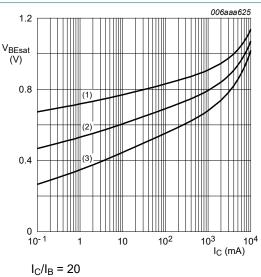


Fig. 7. Base-emitter voltage as a function of collector current; typical values

(2) T_{amb} = 25 °C (3) T_{amb} = 100 °C



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

80 V, 4.6 A NPN low VCEsat transistor

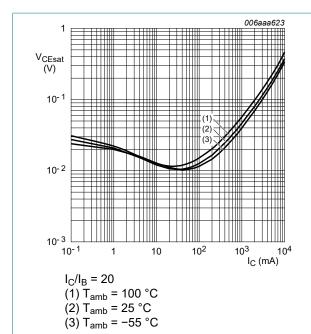


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

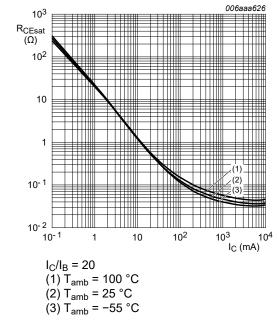


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

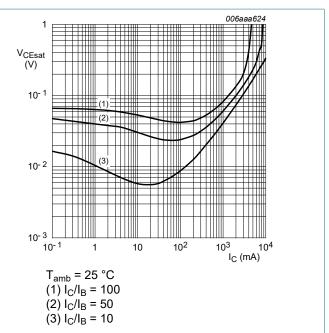


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

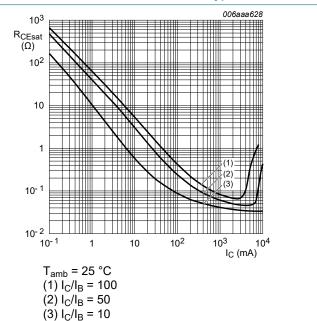
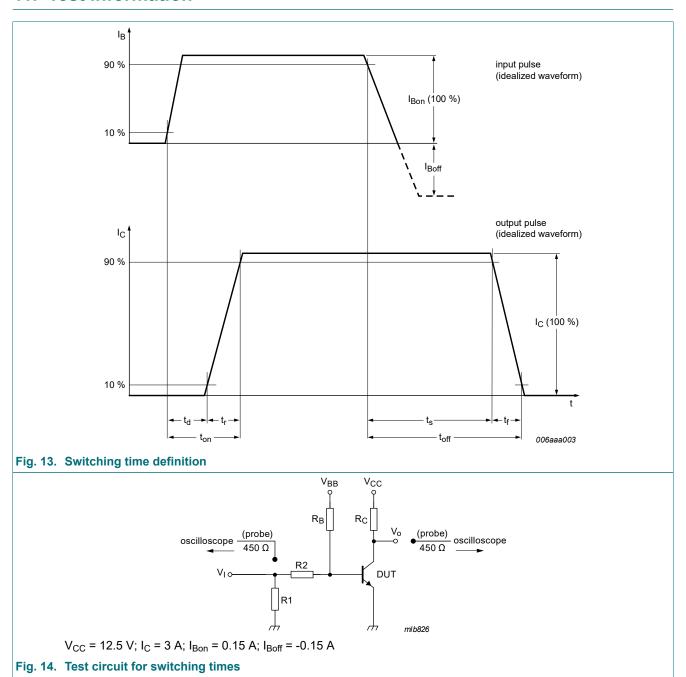


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

80 V, 4.6 A NPN low VCEsat transistor

11. Test information

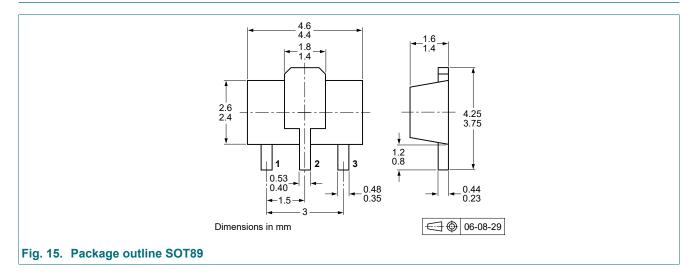


Quality information

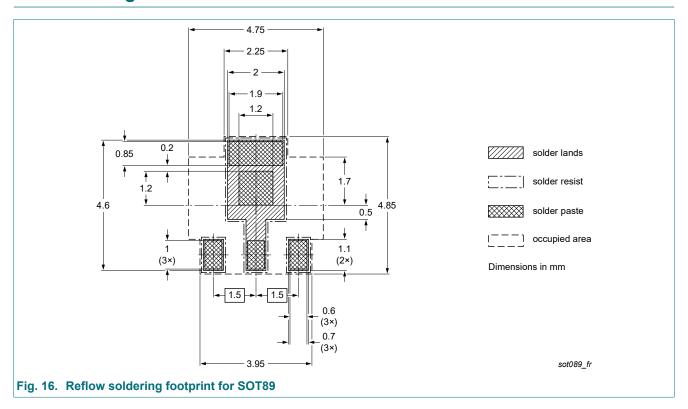
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

80 V, 4.6 A NPN low VCEsat transistor

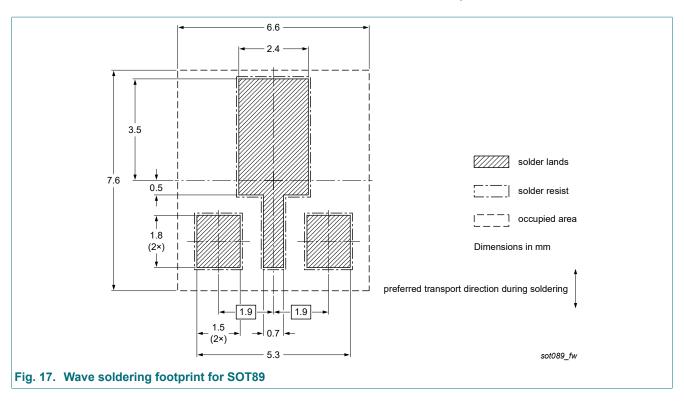
12. Package outline



13. Soldering



80 V, 4.6 A NPN low VCEsat transistor



80 V, 4.6 A NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | |
|----------------|-----------------------------|---|---------------|-------------|--|--|
| PBSS305NX v.3 | 20240214 | Product data sheet | - | PBSS305NX_2 | | |
| Modifications: | Nexperia. • Legal texts hav | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. | | | | |
| PBSS305NX_2 | 20091208 | Product data sheet | - | PBSS305NX_1 | | |
| PBSS305NX_1 | 20060817 | Product data sheet | - | - | | |

80 V, 4.6 A NPN low VCEsat transistor

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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80 V, 4.6 A NPN low VCEsat transistor

Contents

| 1. | General description | 1 |
|-----|-------------------------|----|
| 2. | Features and benefits | 1 |
| 3. | Applications | 1 |
| 4. | Quick reference data | 1 |
| 5. | Pinning information | 2 |
| 6. | Ordering information | 2 |
| 7. | Marking | 2 |
| 8. | Limiting values | 3 |
| 9. | Thermal characteristics | 4 |
| 10 | . Characteristics | 6 |
| 11. | . Test information | 9 |
| 12 | . Package outline | 10 |
| | . Soldering | |
| | . Revision history | |
| | . Legal information | |
| | | |

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 14 February 2024

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